In the Claims:

Claims 1-32 (Cancelled)

33. (Currently amended) A method for forming a layer on a wafer, the method comprising ~~the steps of~~:

placing the wafer onto a pedestal within a chamber, wherein the chamber includes an isolation ring positioned around a periphery of the pedestal; ~~, and wherein the~~ biasing the pedestal ~~is biased to~~ with a first bias power; ~~and~~

biasing a ~~second region~~ target of the chamber ~~to~~ with a second bias power; and

biasing a coil of the chamber with a third bias power, wherein the isolation ring electrically decouples the first bias power from the second and third bias ~~power~~ powers, and wherein ~~portions~~ a top portion of the isolation ring that is exposed to a chamber environment during forming the layer ~~are~~ is coated with a conductive material prior to forming the layer on the wafer, and further wherein biasing the coil with the third bias power includes selectively powering the coil at least once during formation of the layer with a bias waveform to tune stress characteristics of the layer to have at least one portion with a tensile different from another portion.

34. (Original) The method of claim 33, wherein the conductive material is aluminum.

35. (Original) The method of claim 34, wherein the aluminum is flame sprayed onto the isolation ring.

36. (Original) The method of claim 33, wherein the isolation ring includes a ceramic material.

37. (Original) The method of claim 33, wherein the second bias power is a ground potential.

Claims 38-44 (Cancelled)

45. (Previously Presented) The method of claim 33, wherein the layer is further characterized as a barrier layer.

46. (Previously Presented) The method of claim 45, wherein the barrier layer is further characterized as a tantalum-containing barrier layer

47. (Previously Presented) The method of claim 33, wherein the aluminum is arc sprayed onto the isolation ring.

48. (Currently Amended) A method for forming a layer on a wafer, the method comprising ~~the steps of~~:

placing the wafer within a sputtering chamber, wherein the chamber includes an isolation ring ~~that is~~ , the isolation ring having a top portion exposed to an environment of the sputtering chamber coated with a conductive material and having a bottom portion for contacting with the wafer and isolating the wafer from portions of the sputtering chamber;

biasing a coil of the chamber with a bias power, wherein biasing the coil with the bias power includes selectively powering the coil at least once during formation of the layer with a bias waveform to tune stress characteristics of the layer to have at least one portion with a tensile different from another portion; and

biasing a sputtering target for depositing material from ~~a~~ the sputtering target onto the wafer to form the layer.

49. (Previously Presented) The method of claim 48, wherein the conductive material is aluminum.

50. (Previously Presented) The method of claim 49, wherein the aluminum is flame sprayed onto the isolation ring.

51. (Previously Presented) The method of claim 49, wherein the aluminum is arc sprayed onto the isolation ring.

52. (Previously Presented) The method of claim 48, wherein the isolation ring includes a ceramic material.

53. (Previously Presented) The method of claim 48, wherein the isolation ring includes a dielectric material.

54. (New) The method of claim 33, wherein the at least one portion with a tensile different from another portion includes at least one of a first tensile greater than a second tensile and a first tensile less than a second tensile.

55. (New) The method of claim 33, wherein the bias waveform includes at least one selected from the group consisting of a step function waveform, triangle-shaped waveform, sinusoidal waveform, logarithmic power curve, exponential power curve, combinations thereof, and analog, continuous, and quantized waveforms to produce different types of stress characteristics.

56. (New) The method of claim 48, wherein the at least one portion with a tensile different from another portion includes at least one of a first tensile greater than a second tensile and a first tensile less than a second tensile.

57. (New) The method of claim 48, wherein the bias waveform includes at least one selected from the group consisting of a step function waveforms, triangle-shaped waveform, sinusoidal waveform, logarithmic power curve, exponential power curve, combinations thereof, and analog, continuous, and quantized waveforms to produce different types of stress characteristics.